**YE Inspection Recipe 命名规则**

**202202-蔡坤**

* **目的Purpose：**YE inspection recipe naming rule
* **适用范围Applications：**YE 相关的inspection recipe
* **具体内容Content：**

1. 对于FAB YE inspection recipe naming rule的规定，基本格式为：**AAAA\_BBBB\_CCCC**
2. **AAAA**: 产品号 (如：0001)，仅为流水号不包括其他信息

若为了区分同一产品不同版本的recipe信息，可在AAAA后加入最多2个字符的版本信息字母，如无版本区分则无需加入。

如R001\_AA\_ASI和R001A\_AA\_ASI，或者如R001\_P1\_ASI及R001FF\_P1\_ASI

1. **BBBB**: layer or material (如：AA, SPA, DPR…)
2. **CCCC**: action (如：ASI, ADI, CMP…)，详见下表：

|  |  |  |
| --- | --- | --- |
| **Number** | **Module process** | **对应YE action naming** |
| 1 | Film deposition | DEP |
| 2 | Surface clean | CLEAN |
| 3 | Photo | ADI |
| 4 | After Etch | AEI |
| 5 | Pull back | PB |
| 6 | Etch back | EB |
| 7 | Implant | IMP/IMP1/IMP2/IMP3 |
| 8 | Post Asher | ASH |
| 9 | PR strip | ASI |
| 10 | Anneal | ANL/RTP/RTA |
| 11 | CMP | CMP |
| 12 | Remove | RM |
| 13 | APF DEP | APF |
| 14 | DARC | DARC |
| 15 | After WET strip | AWI |
| 16 | Metal B/S | BS |
| 17 | Pre-Clean | PRCLN |
| 18 | Wafer start | START |
| 19 | CAP OX | CAP |

1. 对于一些有特殊要求的scan recipe naming rule后缀的规定是在**CCCC**后加入后缀，基本为格式为：**AAAA\_BBBB\_CCCC\_DDDD，DDDD**详见下表：

|  |  |  |
| --- | --- | --- |
| 1 | Wafer edge scan | \_ED |
| 2 | 只对SRAM扫描 | \_SRAM |
| 3 | e-beam scan站点 | \_EB |
| 4 | LITHO PWQ 验证 | \_PWQ |
| 5 | LITHO FEM 验证 | \_FEM |
| 6 | Short loop recipe | \_SLP |
| 7 | PCM recipe | \_PCM |
| 8 | 工程实验recipe | \_ENG |
| 9 | Print down recipe | \_PDR |
| 10 | Wafer破片确认impact | \_WB |
| 11 | BFI 50% coverage recipe | \_F |
| 12 | BFI 25% coverage recipe | \_Q |
| 13 | BFI 12.5% coverage recipe | \_H |
| 14 | Finetune recipe后，备份老recipe | \_BK |

1. 扫描Bare wafer的 recipe为 BARE\_SI
2. 机台monitor recipe 命名规则

格式**DM\_AAAA\_BBBB**, DM: Daily monitor 简写

**AAAA**: 机台名称（如：AMBFI01）

**BBBB**: Monitor 类别，Capture rate为“CR”；Particle monitor为“PD”例如：DM\_ ALBFI01\_CR

1. 事项说明

所有YE人员必须按照本规定来命名Inspection Recipe。如有其他新的process 出现而本规定没有定义的情况，请与文件所有人联系并更新本文件。